Form PTO 1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY DOCKET NO.		SERIAL NO.			
(Modified)		25		249979US2S	10/792,324				
		4 E 2		APPLICANT					
LIST OF	REPERENCES CHED BY APPLICANT			Yuui SHIMIZU					
	Ya.	12 m [5]		FILING DATE March 4, 2004		GROUP 2827			
	TEN	Te TRADENT		U.S. PATENT DOCUMENTS					
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILI IF API	NG DATE PROPRIATE	
HU	AA	6,081,445	06/27/2000	J. SHI, et al.					
	AB						•		
	AC		·						
	AD								
	AE								
	AF			·	I				
	AG								
	AH								
	Al	·							
	AJ								
	AK	·							
	AL								
	AM								
	AN	1			1				
		*	FO	REIGN PATENT DOCUMENTS					
		DOCUMENT DATE COUNTRY				TRANSLATION			
		NUMBER	DATE	COUNTRY		YES	3	NO	
144	AO	2003-242771	08/29/2003	JAPAN				X	
	AP								
	AQ								
	AR				··	·			
	AS							·	
	AT					·		····	
	AU	<u> </u>							
	AV		<u></u>						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)									
tht	AW	R. SCHEUERLEIN, et al., IEEE International Solid-State Circuits Conference, Digest paper, pages 128-129, "TA 7.2 A 10NS READ AND WRITE NON-VOLATILE MEMORY ARRAY USING A MAGNETIC TUNNEL JUNCTION AND FET SWITCH IN EACH CELL", 2000							
HH	AX	M. DURLAM, et al., IEEE International Solid-State Circuits Conference, Digest Paper, pages 130-131, "TA 7.3 NONVOLATILE RAM BASED ON MAGNETIC TUNNEL JUNCTION ELEMENTS", 2000							
	AY								
	AZ		Additional References sheet(s) attache						
Examiner	to an q					Date Considered 6/20/05			
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.									